Design Rules

(1) Metal & Diffusion have min^{m} width & Spacing of 4λ

(2) Contacts are 2λ × 2λ and must be surrounded by 1λ on the layers above and below.

(3) Poly Si uses a width of 2λ

(4) Poly Si overlops diff. by 2λ where transistor is desired and has a spacing of λ away where no transistor is desired

(5) Poly Si and contacts have a spacing of 3λ from other ~~poly Si~~ poly Si or contacts

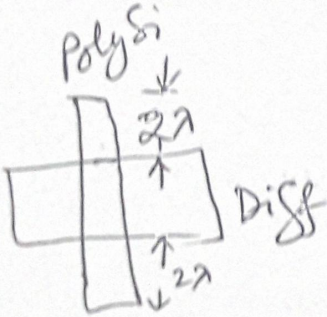
(6) N-well surrounds pMOS transistors by 6λ and avoids nMOS transistor by 6λ

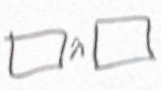
Design Rules

- Contact cut → $2\lambda \times 2\lambda$
- Contact cut to diffusion → λ
- diffusion to depletion Implant 2λ

Metal length = 4λ
Metal to Metal distance ⇒ 4λ
N-well to p-diffusion ⇒ 6λ
N-well to n-diff ⇒ 6λ

poly Si width ⇒ 2λ





* Contact to Contact λ distance Min^m রাখতে হবে
* Metal 1, Metal 2 use করলে, সবসময় short না হয়
* Poly, Poly overlap করলে short; Diff, Diff short হয়